

**• General Description**

The ZM120P04D combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . This device is ideal for load switch and battery protection applications.

**• Features**

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

**• Application**

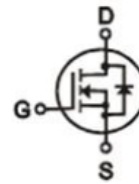
- MB/VGA Vcore
- SMPS 2<sup>nd</sup> Synchronous Rectifier
- POL application
- BLDC Motor driver

**• Ordering Information:**

Part NO.	ZM120P04D
Marking	ZM120P04
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

**• Absolute Maximum Ratings (  $T_c = 25^\circ\text{C}$  )**

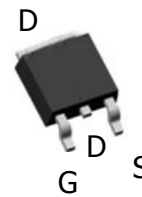
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-40	V
Gate-Source Voltage	$V_{GS}$	$\pm 25$	V
Continuous Drain Current	$I_{D@TC=25^\circ\text{C}}$	-45	A
	$I_{D@TC=75^\circ\text{C}}$	-34	A
	$I_{D@TC=100^\circ\text{C}}$	-28	A
Pulsed Drain Current <sup>①</sup>	$I_{DM}$	-135	A
Total Power Dissipation	$P_{D@TC=25^\circ\text{C}}$	50	W
Total Power Dissipation	$P_{D@TA=25^\circ\text{C}}$	1.25	W
Operating Junction Temperature	$T_J$	-55 to 150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 to 150	$^\circ\text{C}$

**• Product Summary**


$V_{DS} = -40\text{V}$

$R_{DS(ON)} = 12\text{m}\Omega$

$I_D = -45\text{A}$



TO-252



Single Pulse Avalanche Energy	$E_{AS}$	100	mJ
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**•Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.3	°C/W
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	50	°C/W
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	°C

**•Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-40			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\mu A$	-1.2		-2.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = -40V, V_{GS} = 0V$			1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -3A$		12	15.6	m $\Omega$
		$V_{GS} = -4.5V, I_D = -2A$		15	19.5	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = -10V, I_D = -2A$		18		s

**•Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	$C_{iss}$	f = 1MHz	-	2750	-	pF
Output capacitance	$C_{oss}$		-	185	-	
Reverse transfer capacitance	$C_{rss}$		-	135	-	

**•Gate Charge characteristics( $T_a = 25^\circ C$ )**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	$Q_g$	$V_{DD} = 25V$	-	30	-	nC
Gate - Source charge	$Q_{gs}$	$I_D = 5A$	-	9	-	
Gate - Drain charge	$Q_{gd}$	$V_{GS} = 10V$	-	15	-	

Note: ① Pulse Test : Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$  ;

Fig.1 Gate-Charge Characteristics

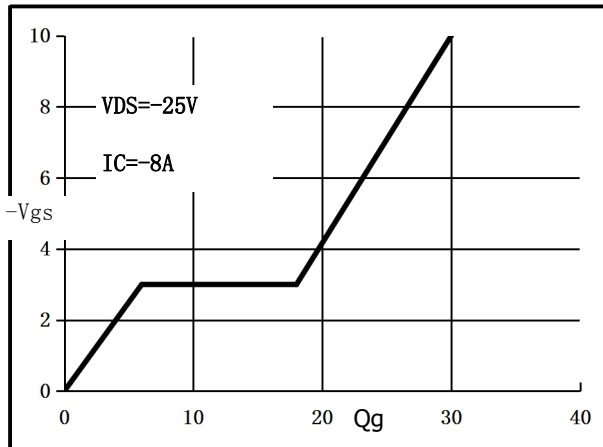


Fig.2 Capacitance Characteristics

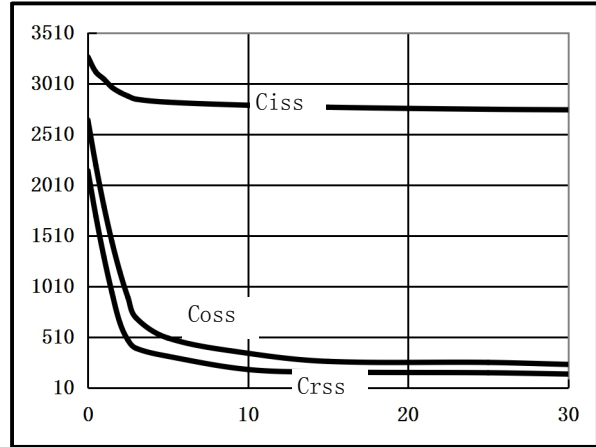


Fig.3 Power Dissipation Derating Curve

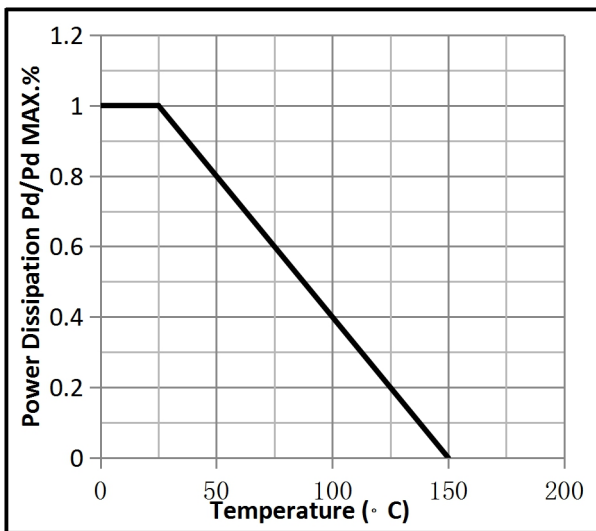


Fig.4 Typical output Characteristics

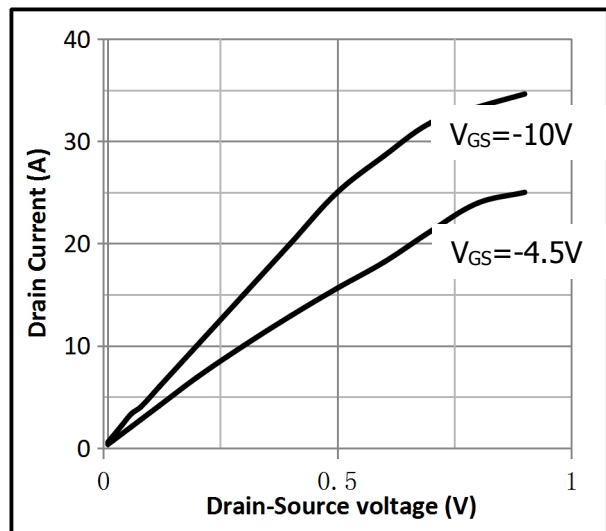


Fig.5 Threshold Voltage V.S Junction Temperature

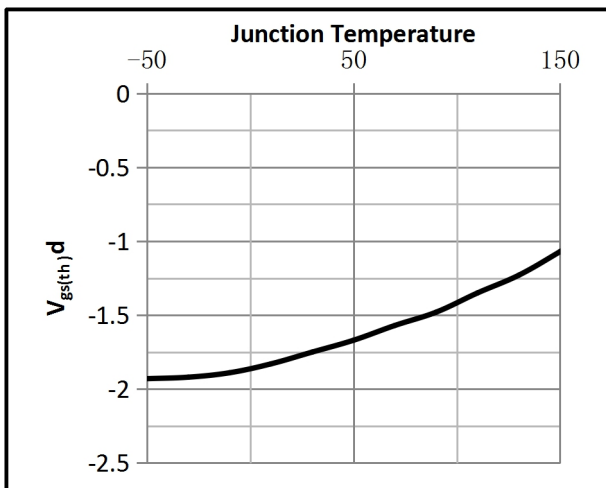


Fig.6 Resistance V.S Drain Current

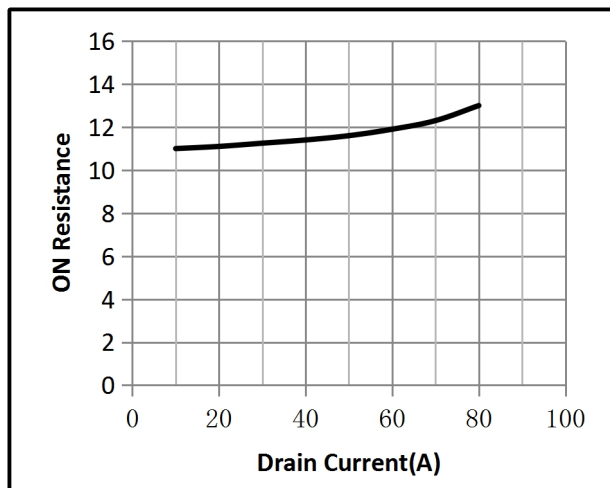


Fig.7 On-Resistance VS Gate Source Voltage

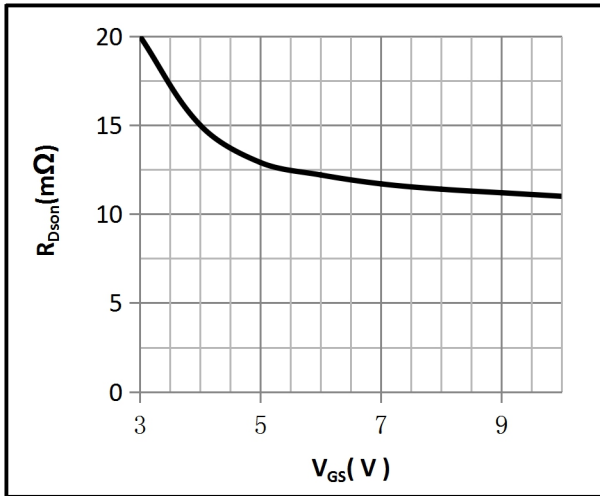


Fig.8 On-Resistance V.S Junction Temperature

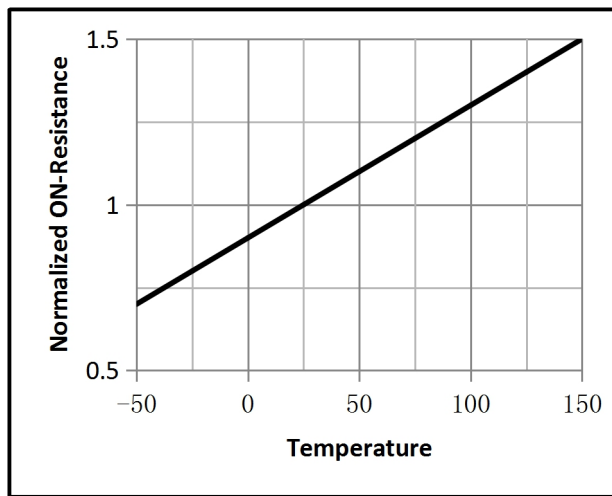


Fig.7 Switching Time Measurement Circuit

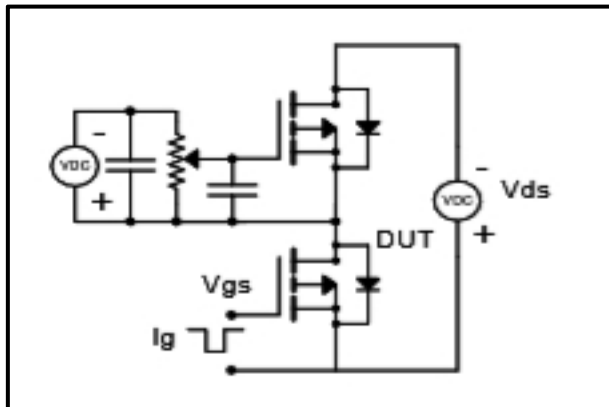


Fig.8 Gate Charge Waveform

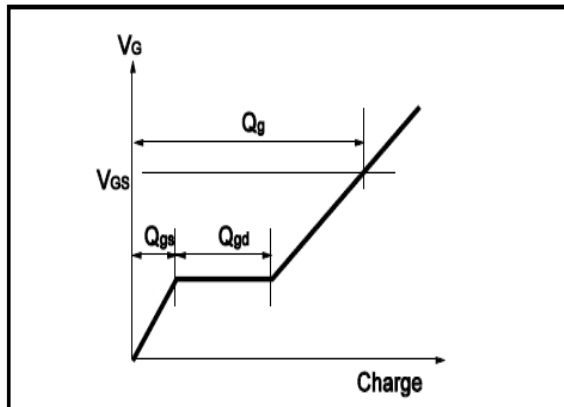


Fig.9 Switching Time Measurement Circuit

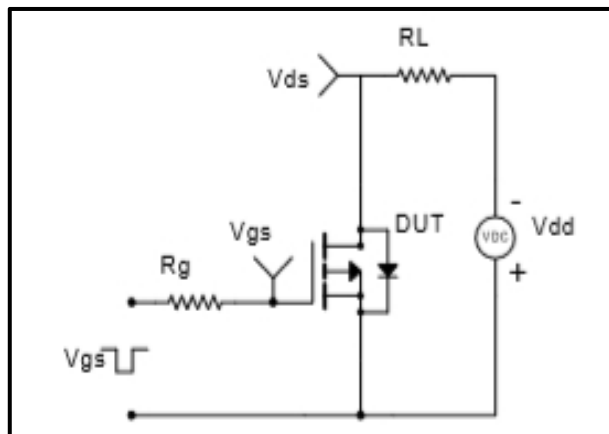


Fig.10 Gate Charge Waveform

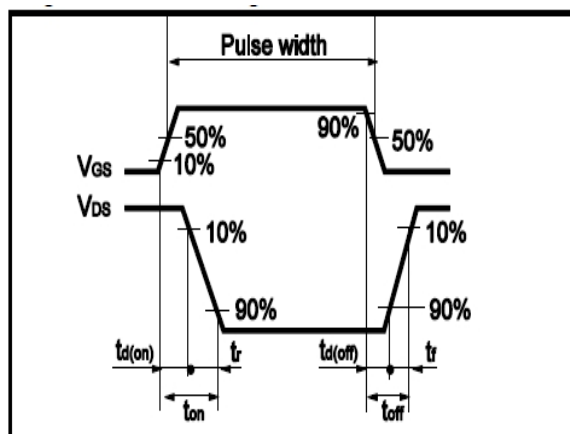


Fig.11 Avalanche Measurement Circuit

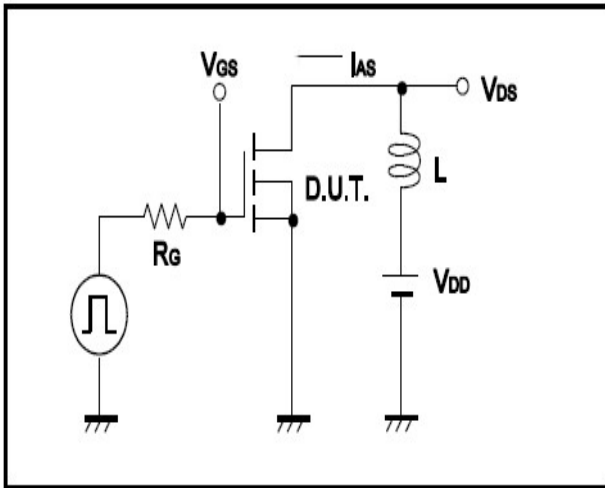
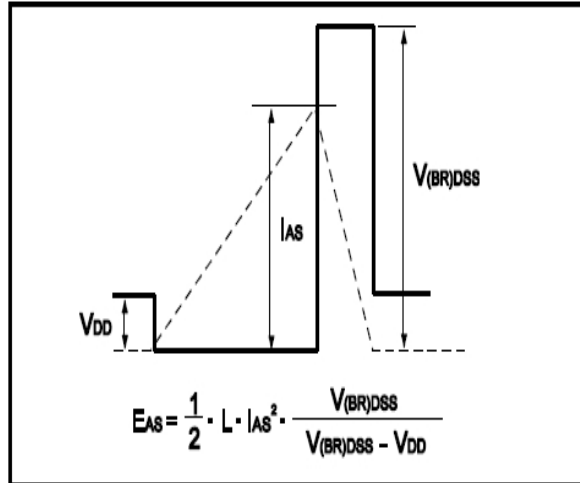


Fig.12 Avalanche Waveform

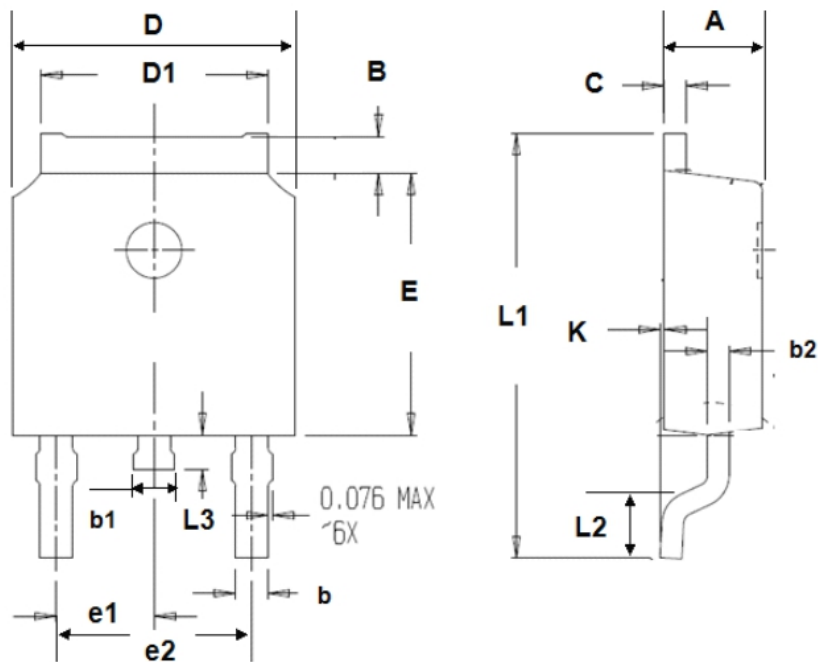




•Dimensions(TO-252)

Unit: mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			



单击下面可查看定价，库存，交付和生命周期等信息

[>>ZMJSEMI](#)